

PST #2.
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			
INFORMATION DISCLOSURE STATEMENT		Docket Number: 01381/8	
Application Number 10/509,923	Filing Date October 1, 2004	Examiner Not Yet Assigned	Art Unit Not Yet Assigned
Title SEED CRYSTAL CONSISTING OF SILICON CARBIDE SINGLE CRYSTAL AND METHOD FOR PRODUCING INGOT USING THE SAME		Applicant(s) Noboru OHTANI et al.	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on

Date: DECEMBER 1, 2004 Reg. No. 29,182

Signature: John J. Kelly, Jr.
John J. Kelly, Jr.

1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorney(s) for Applicant(s) hereby bring the reference(s) listed on the attached modified PTO Form No. 1449 to the attention of the Examiner. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

2. A copy of each patent, publication or other information listed on the modified PTO form 1449 is enclosed, except as otherwise indicated.

3. It is believed that no fees are due in connection with this Information Disclosure Statement. However, should any fees be due, the Commissioner is authorized to charge Deposit Account No. 11-0600 for such fees. A duplicate copy of this communication is enclosed for charging purposes.

Dated: December 1, 2004

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PATENT AND TRADEMARK OFFICE

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
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01381/8SERIAL NO.
10/509,923APPLICANT
Noboru OHTANI et al.FILING DATE
October 1, 2004GROUP
Not Yet Assigned**U. S. PATENT DOCUMENTS**

EXAMINER INITIAL	PATENT/PUBLICATION NUMBER	PATENT/PUBLICATION DATE	NAME	CLASS	SUBCLASS	FILING DATE*
	5,958,132	September 28, 1999	Takahashi et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						Yes	No
	JP 10-17399	January 20, 1998	Japan			Abstract	
	JP 11-106297	April 20, 1999	Japan			Abstract	

OTHER DOCUMENTS

EXAMINER INITIAL		AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
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		P. G. Neudeck et al., Performance Limiting Micropipe Defects in Silicon Carbide Wafers, IEEE Electron Device Letters, Vol. 15 (1994) pp. 63-65.
		T. Kimoto et al., Performance Limiting Surface Defects in SiC Epitaxial p-n Junction Diodes, IEEE Tran. Electron. Devices, Vol. 46 (1999) pp. 471-477.
		J. Takahashi et al., Sublimation Growth of SiC Single Crystalline Ingots on faces Perpendicular to the (0001) Basal Plane, J. Cryst. Growth, Vol. 135 (1994) pp. 61-70.
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		J. Takahashi et al., Sublimation Growth of 6H- and 4H-SiC Single Crystals in the [1100] and [1120] Directions, Journal of Crystal Growth, Vol. 181 (1997) pp. 229-240.
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		Japanese Patent Application Laid-open No. 5-262599, SiC Single Crystal and Method for Growing the Same, October 12, 1993.

EXAMINER	DATE CONSIDERED
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	